

# 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



# **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# BTA212 series B Three quadrant triacs high commutation

**Product specification** 

September 1997



# Three quadrant triacs high commutation

## BTA212 series B

## **GENERAL DESCRIPTION**

Glass passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

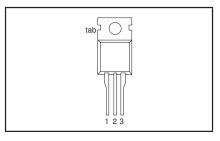
## **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
$V_{DRM}$	BTA212- Repetitive peak off-state	<b>500B</b> 500	<b>600B</b> 600	<b>800B</b> 800	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	voltages RMS on-state current Non-repetitive peak on-state current	12 95	12 95	12 95	A A

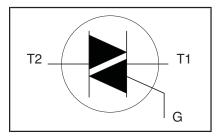
## **PINNING - TO220AB**

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

#### **PIN CONFIGURATION**



## **SYMBOL**



## **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V <sub>DRM</sub>	Repetitive peak off-state voltages		-	<b>-500</b> 500 <sup>1</sup>	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave;	-		12		Α
I <sub>TSM</sub>	Non-repetitive peak on-state current	$T_{mb} \le 99 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge					
		t = 20 ms	-		95 105		A
l <sup>2</sup> t dl <sub>T</sub> /dt	l <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	$ \begin{aligned} &t = 16.7 \text{ ms} \\ &t = 10 \text{ ms} \\ &I_{TM} = 20 \text{ A}; \ I_{G} = 0.2 \text{ A}; \\ &dI_{G}/dt = 0.2 \text{ A}/\mu\text{s} \end{aligned} $	-		105 45 100		A A²s A/μs
I <sub>GM</sub> V <sub>GM</sub> P <sub>GM</sub> P <sub>G(AV)</sub>	triggering Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms	- - -		2 5 5 0.5		A V W W
$egin{array}{c} T_{\text{stg}} \\ T_{j} \end{array}$	Storage temperature Operating junction temperature	period	-40 -		150 125		°C °C

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	-	- - 60	1.5 2.0 -	K/W K/W K/W

## STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		T2+ G+	2	18	50	mA
		T2+ G-	2	21	50	mA
		T2- G-	2	34	50	mA
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
		T2+ G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	31	60	mA
$V_{T}^{I_{H}}$	On-state voltage	$I_T = 17 \text{ A}$	-	1.3	1.6	V
V <sub>GT</sub>	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
$I_{D}$	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125$ °C	-	0.1	0.5	mA

# **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/μs
	off-state voltage Critical rate of change of commutating current	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 12 \text{ A};$ without snubber; gate open circuit	-	24	-	A/ms
t <sub>gt</sub>	Gate controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

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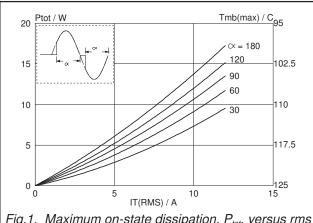


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

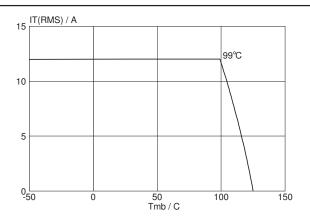


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

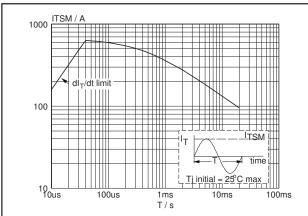


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

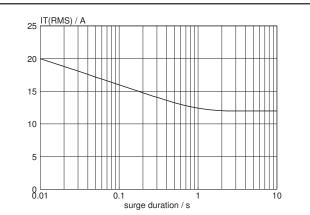


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 99$ °C.

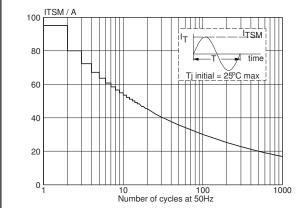


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

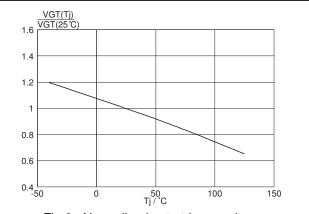
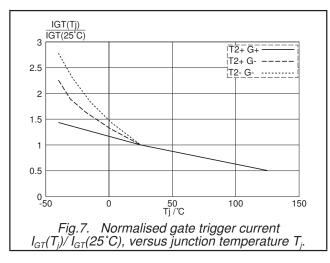


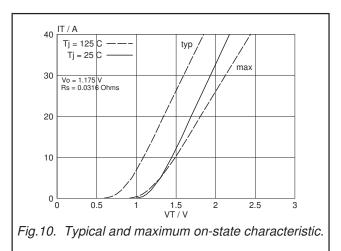
Fig.6. Normalised gate trigger voltage  $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_i$ .

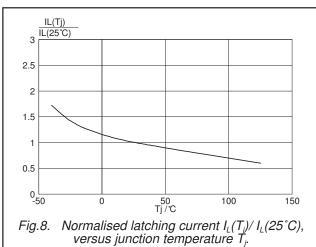
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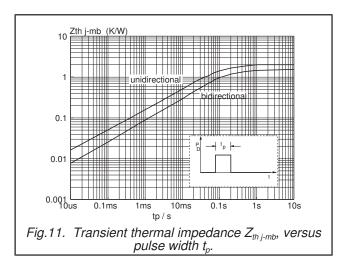
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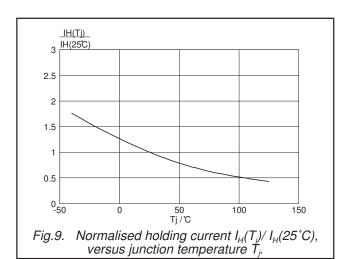
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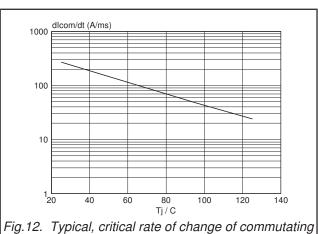












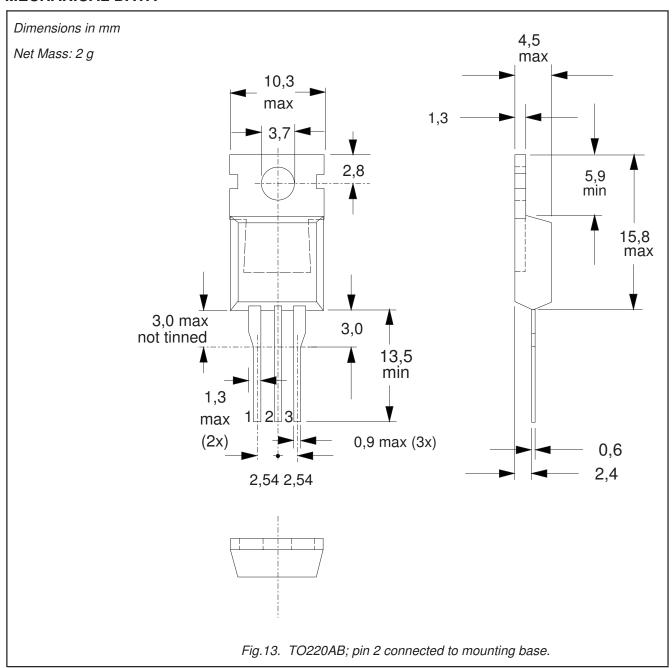
| Fig.12. Typical, critical rate of change of commutating current dl<sub>com</sub>/dt versus junction temperature.

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# Three quadrant triacs high commutation

BTA212 series B

## **MECHANICAL DATA**



- Refer to mounting instructions for TO220 envelopes.
   Epoxy meets UL94 V0 at 1/8".

# Legal information

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet Production This document contains the product specification.		This document contains the product specification.

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